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CAPACITOR AND FORMING METHOD THEREOF

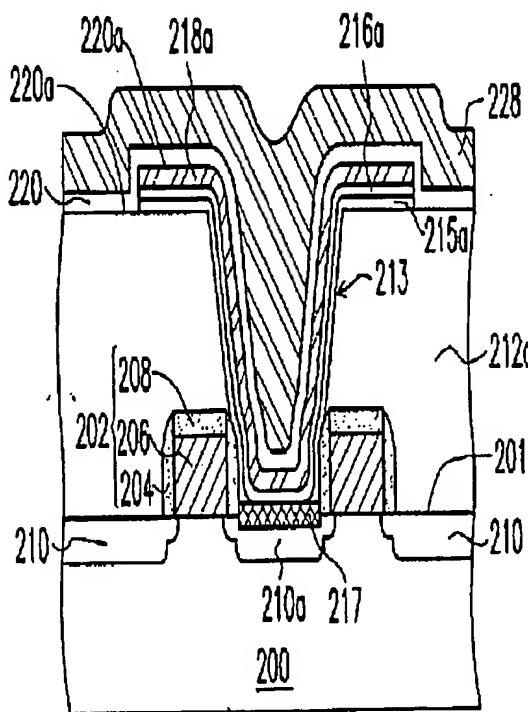
Representative drawing

(57) Abstract:

PURPOSE: A capacitor and forming method thereof is provided to solve problem of micro-loading, increase a conductive region, and simplify manufacturing process.

CONSTITUTION: A substrate comprises two gates and a common source/drain region. A part of the common source/drain region is exposed by forming a pitted self align contact window(PSACW) using self align contact process. A glue/barrier layer and a lower electrode of a capacitor are formed on the pitted self contact window. A dielectric thin film is formed on a lower electrode. An upper electrode is formed on the dielectric thin film.

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